

2SK2377

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

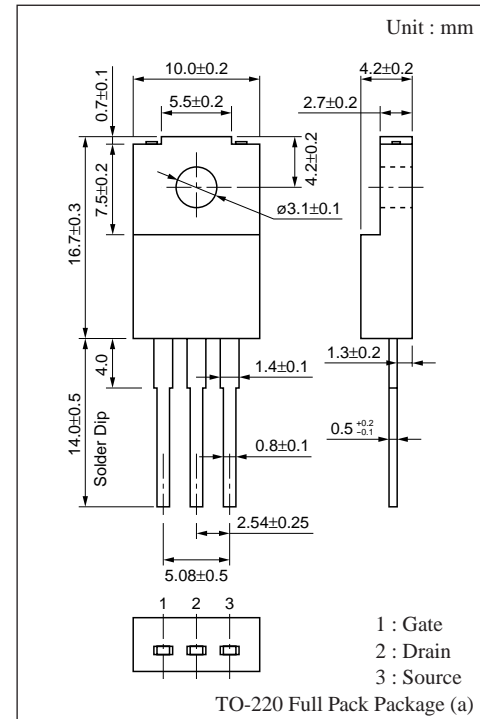
■ Absolute Maximum Ratings (T_c = 25°C)

Parameter	Symbol	Rating	Unit	
Drain-Source breakdown voltage	V _{DSS}	170	V	
Gate-Source voltage	V _{GS}	±20	V	
Drain current	DC	I _D	±20	A
	Pulse	I _{DP}	±40	A
Avalanche energy capability	EAS*	200	mJ	
Allowable power dissipation	T _c = 25°C	P _D	50	W
	T _a = 25°C		2	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

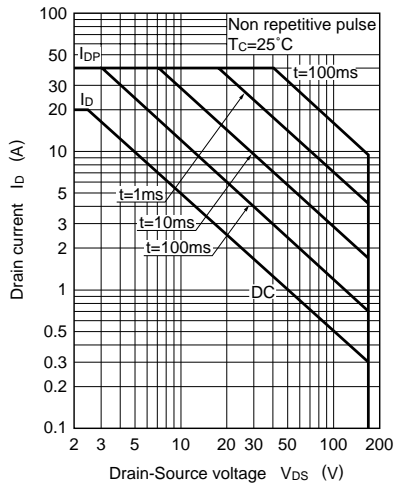
* L=1mH, I_L= 20A, 1 pulse

■ Electrical Characteristics (T_c = 25°C)

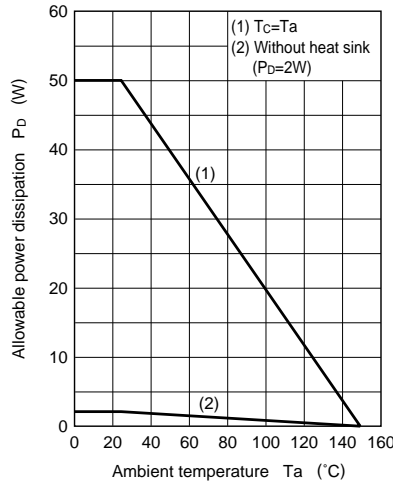
Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Drain-Source cut-off current	I _{DSS}	V _{DS} =140V, V _{GS} = 0			10	μA	
Gate-Source leakage current	I _{GS}	V _{GS} =±20V, V _{DS} = 0			±1	μA	
Drain-Source breakdown voltage	V _{DSS}	I _D =1mA, V _{GS} = 0	170			V	
Gate threshold voltage	V _{th}	V _{DS} =10V, I _D =1mA	1		2.5	V	
Drain-Source ON-resistance	R _{DS(on)1}	V _{GS} =10V, I _D =10A		95	145	mΩ	
	R _{DS(on)2}	V _{GS} = 4V, I _D =10A		105	160	mΩ	
Forward transadmittance	Y _{fs}	V _{DS} =10V, I _D =10A	10	17		S	
Diode forward voltage	V _{DSF}	I _{DR} =20A, V _{GS} = 0			-1.6	V	
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} = 0, f=1MHz		1650		pF	
Output capacitance	C _{oss}			400		pF	
Feedback capacitance	C _{rss}			130		pF	
Turn-on time (delay time)	t _{d(on)}				10		ns
Rise time	t _r		V _{DD} =100V, I _D =10A		60		ns
Fall time	t _f	V _{GS} =10V, R _L =10Ω		280		ns	
Turn-off time (delay time)	t _{d(off)}			1500		ns	
Channel-Case heat resistance	R _{th(ch-c)}				2.5	°C/W	
Channel-Atmosphere heat resistance	R _{th(ch-a)}				62.5	°C/W	



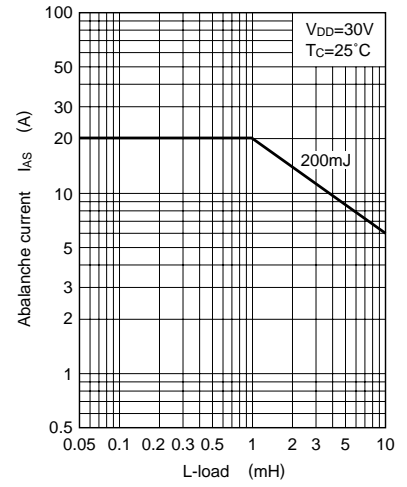
Area of safe operation (ASO)



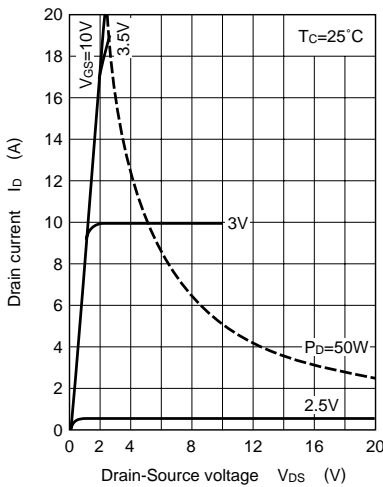
$P_D - T_a$



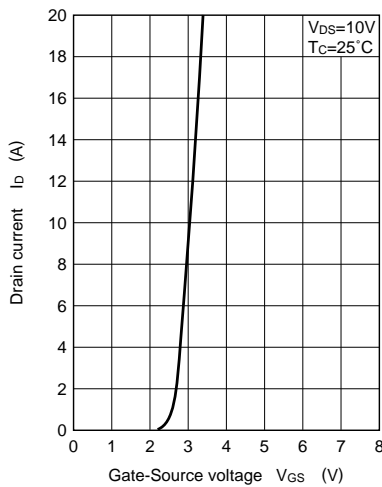
IAS - L-load



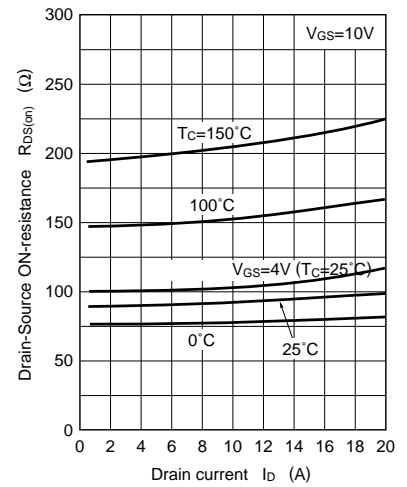
$I_D - V_{DS}$



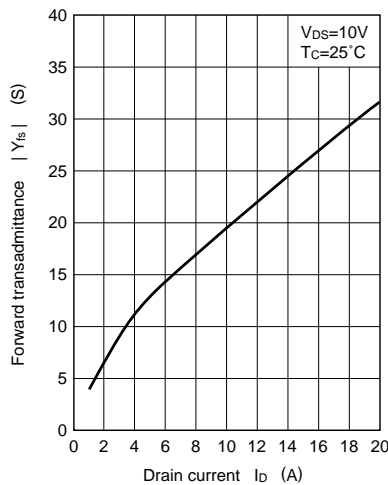
$I_D - V_{GS}$



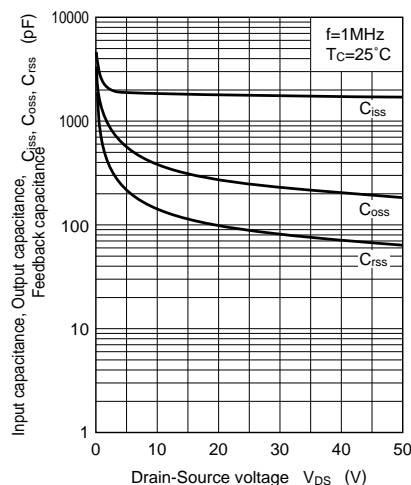
$R_{DS(on)} - I_D$



$|Y_{fs}| - I_D$



$C - V_{DS}$



$I_{GSS} - T_a$

